Dual INT-A-PAK Low Profile "Half Bridge" (Standard Speed IGBT), 300 A

Dual INT-A-PAK Low Profile

PRODUCT SUMMARY	
V_{CES}	600 V
I_C DC at T_C = 25 °C	530 A
$V_{CE(on)}$ (typical) at 300 A, 25 °C	1.24 V
Speed	DC to 1 kHz
Package	DIAP low profile
Circuit	Half bridge

FEATURES

RoHS COMPLIANT

- Gen 4 IGBT technology
- Standard: optimized for hard switching speed
- Low $V_{CE(on)}$
- Square RBSOA
- HEXFRED® antiparallel diode with ultrasoft reverse recovery characteristics
- Industry standard package
- Al_2O_3 DBC
- UL approved file E78996
- Designed for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Increased operating efficiency
- Performance optimized as output inverter stage for TIG welding machines
- Direct mounting on heatsink
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C (1)	T_C = 25 °C	530	A
		T_C = 80 °C	376	
Pulsed collector current	I_{CM}		800	
Clamped inductive load current	I_{LM}		800	
Diode continuous forward current	I_F	T_C = 25 °C	219	
		T_C = 80 °C	145	
Gate to emitter voltage	V_{GE}		± 20	V
Maximum power dissipation (IGBT)	P_D	T_C = 25 °C	1136	W
		T_C = 80 °C	636	
RMS isolation voltage	V_{ISOL}	Any terminal to case (V_{RMS} t = 1 s, T_J = 25 °C)	3500	V

Note

(1) Maximum continuous collector current must be limited to 500 A to do not exceed the maximum temperature of terminals

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Collector to emitter breakdown voltage	$V_{BR(CES)}$	V_{GE} = 0 V, I_C = 500 μA	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	V_{GE} = 15 V, I_C = 150 A	-	1.04	1.15	
		V_{GE} = 15 V, I_C = 300 A	-	1.24	1.45	
		V_{GE} = 15 V, I_C = 150 A, T_J = 125 °C	-	0.96	1.06	
		V_{GE} = 15 V, I_C = 300 A, T_J = 125 °C	-	1.22	1.42	
Gate threshold voltage	$V_{GE(th)}$	V_{CE} = V_{GE}, I_C = 250 μA	2.9	4.8	6.3	
Collector to emitter leakage current	I_{CES}	V_{GE} = 0 V, V_{CE} = 600 V	-	0.02	0.75	mA
		V_{GE} = 0 V, V_{CE} = 600 V, T_J = 125 °C	-	1.5	10	
Diode forward voltage drop	V_{FM}	I_{FM} = 150 A	-	1.23	1.39	V
		I_{FM} = 300 A	-	1.48	1.75	
		I_{FM} = 150 A, T_J = 125 °C	-	1.17	1.33	
		I_{FM} = 300 A, T_J = 125 °C	-	1.50	1.77	
Gate to emitter leakage current	I_{GES}	V_{GE} = ± 20 V	-	-	± 200	nA

SWITCHING CHARACTERISTICS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Turn-on switching loss	E_{on}	I_C = 300 A, V_{CC} = 360 V, V_{GE} = 15 V, R_g = 1.5 Ω, L = 500 μH, T_J = 25 °C	-	9	-	mJ
Turn-off switching loss	E_{off}		-	90	-	
Total switching loss	E_{tot}		-	99	-	
Turn-on switching loss	E_{on}	I_C = 300 A, V_{CC} = 360 V, V_{GE} = 15 V, R_g = 1.5 Ω, L = 500 μH, T_J = 125 °C	-	23	-	
Turn-off switching loss	E_{off}		-	133	-	
Total switching loss	E_{tot}		-	156	-	
Turn-on delay time	$t_{d(on)}$		-	442	-	ns
Rise time	t_r		-	301	-	
Turn-off delay time	$t_{d(off)}$		-	406	-	
Fall time	t_f		-	1570	-	
Reverse bias safe operating area	RBSOA	T_J = 150 °C, I_C = 800 A, V_{CC} = 400 V V_P = 600 V, R_g = 22 Ω, V_{GE} = 15 V to 0 V, L = 500 μH		Fullsquare		
Diode reverse recovery time	t_{rr}	I_F = 300 A, dI_F/dt = 500 A/μs, V_{CC} = 400 V, T_J = 25 °C	-	150	179	ns
Diode peak reverse current	I_{rr}		-	43	59	A
Diode recovery charge	Q_{rr}		-	3.9	6.3	μC
Diode reverse recovery time	t_{rr}	I_F = 300 A, dI_F/dt = 500 A/μs, V_{CC} = 400 V, T_J = 125 °C	-	236	265	ns
Diode peak reverse current	I_{rr}		-	64	80	A
Diode recovery charge	Q_{rr}		-	8.6	11.1	μC

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNITS
Operating junction and storage temperature range		T_J, T_{Stg}	-40	-	150	°C
Junction to case per leg	IGBT	R_{thJC}	-	-	0.11	°C/W
	Diode		-	-	0.4	
Case to sink per module		R_{thCS}	-	0.05	-	
Mounting torque	case to heatsink: M6 screw		4	-	6	Nm
	case to terminal 1, 2, 3: M5 screw		2	-	4	
Weight			-	270	-	g

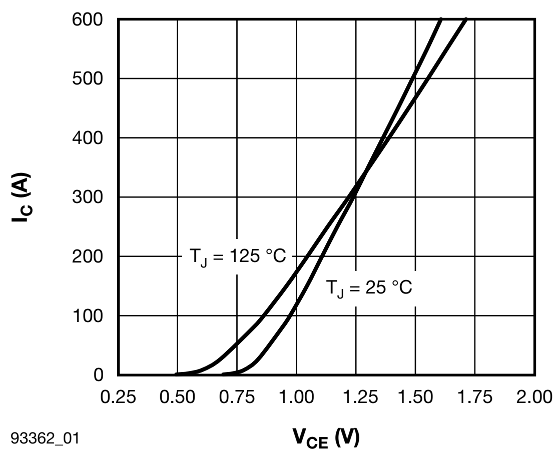


Fig. 1 - Typical Output Characteristics, T_J = 25 °C, V_{GE} = 15 V

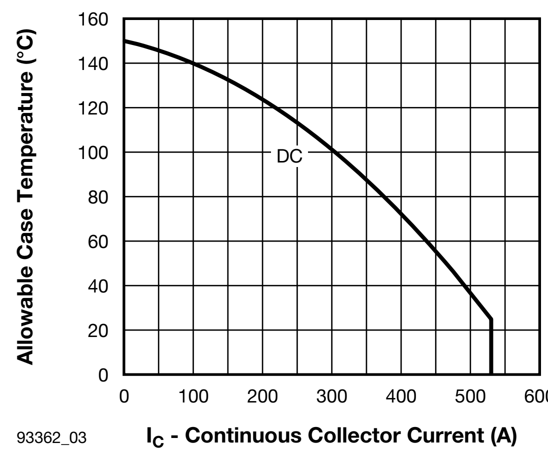


Fig. 3 - Maximum DC IGBT Collector Current vs. Case Temperature

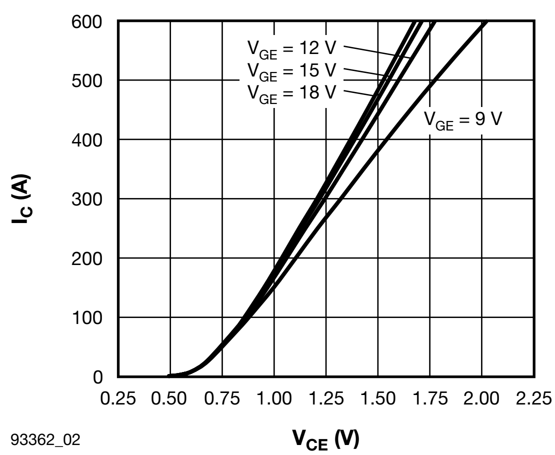


Fig. 2 - Typical Output Characteristics, T_J = 125 °C

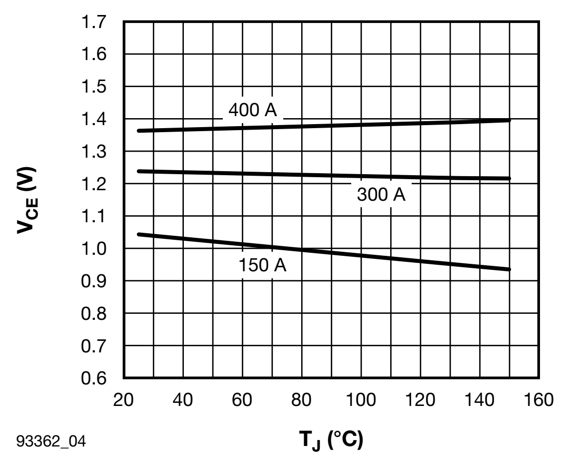


Fig. 4 - Typical IGBT Collector to Emitter Voltage vs. Junction Temperature, V_{GE} = 15 V

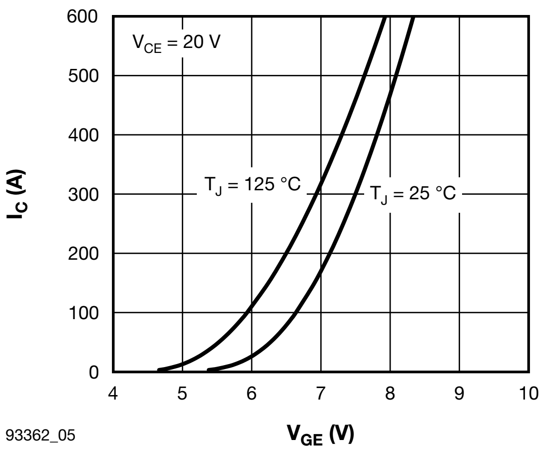


Fig. 5 - Typical IGBT Transfer Characteristics

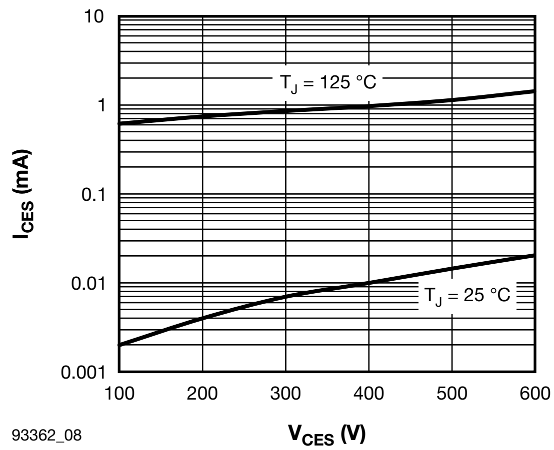


Fig. 8 - Typical IGBT Zero Gate Voltage Collector Current

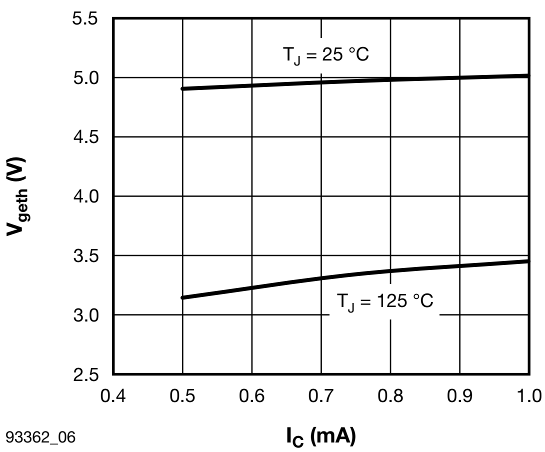


Fig. 6 - Typical IGBT Gate Threshold Voltage

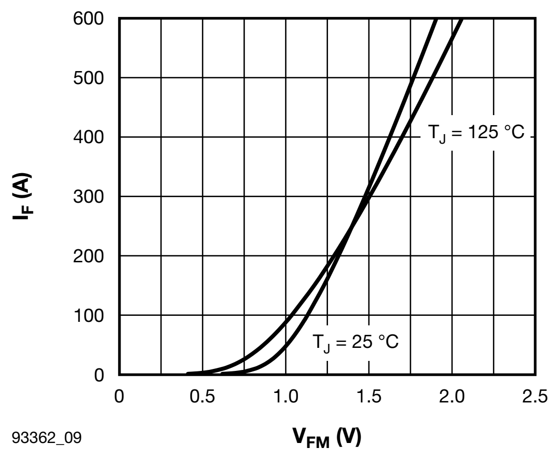


Fig. 9 - Typical Diode Forward Characteristics

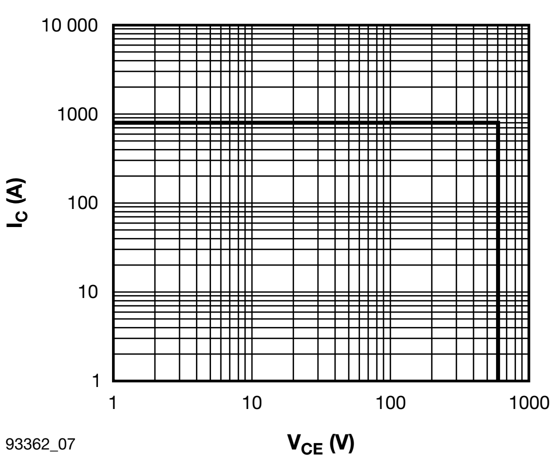


Fig. 7 - IGBT Reverse Bias SOA,
T_J = 150 °C, V_{GE} = 15 V, R_g = 22 Ω

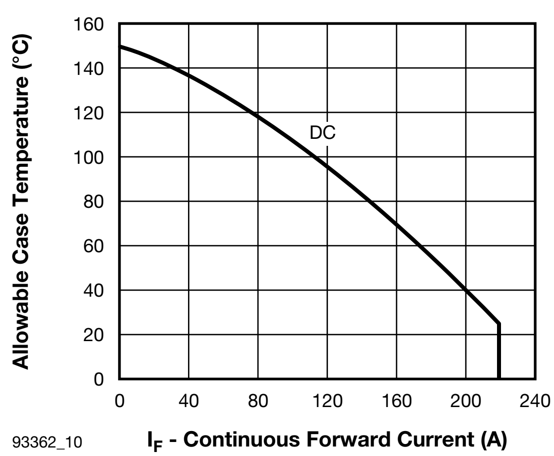


Fig. 10 - Maximum DC Forward Current vs. Case Temperature

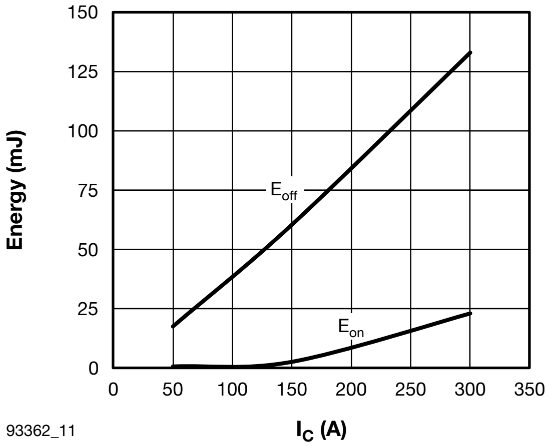


Fig. 11 - Typical IGBT Energy Loss vs. I_C, T_J = 125 °C, V_{CC} = 360 V, R_g = 1.5 Ω, V_{GE} = 15 V, L = 500 μH

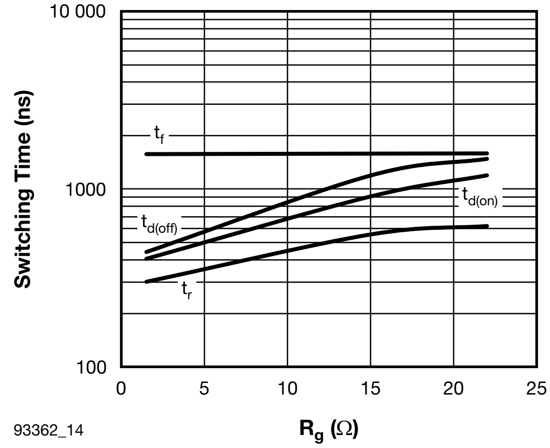


Fig. 14 - Typical IGBT Switching Time vs. R_g, T_J = 125 °C, I_C = 300 A, V_{CC} = 360 V, V_{GE} = 15 V, L = 500 μH

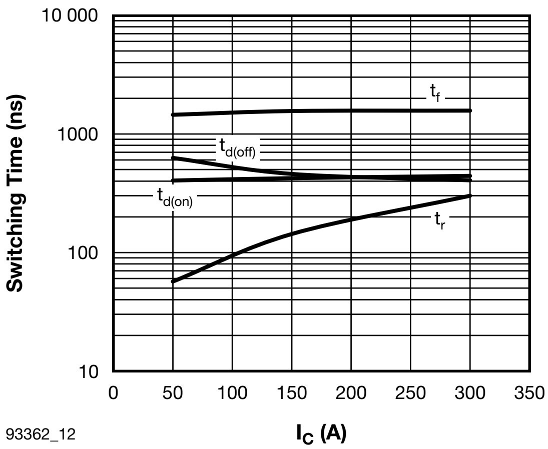


Fig. 12 - Typical IGBT Switching Time vs. I_C, T_J = 125 °C, V_{CC} = 360 V, R_g = 1.5 Ω, V_{GE} = 15 V, L = 500 μH

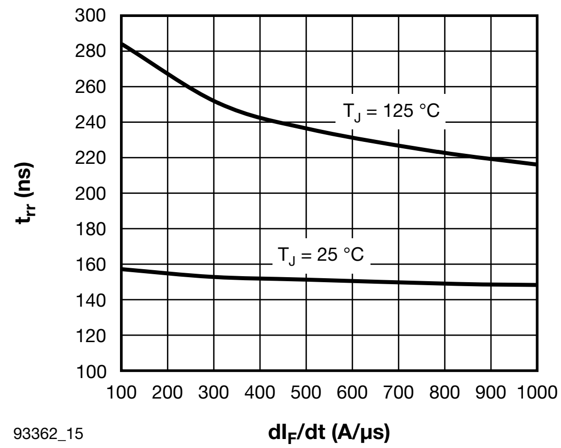


Fig. 15 - Typical Reverse Recovery Time vs. dI_F/dt, V_{CC} = 400 V, I_F = 300 A

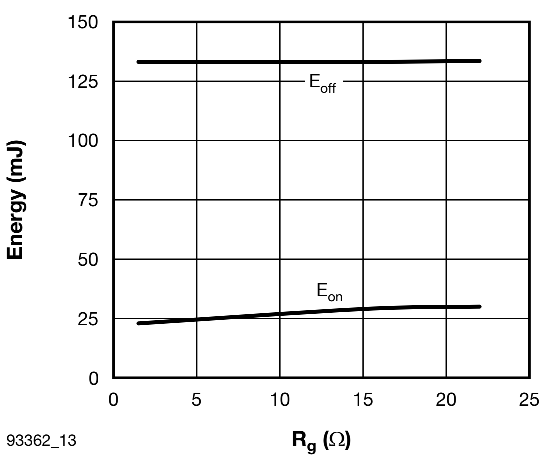


Fig. 13 - Typical IGBT Energy Loss vs. R_g, T_J = 125 °C, I_C = 300 A, V_{CC} = 360 V, V_{GE} = 15 V, L = 500 μH

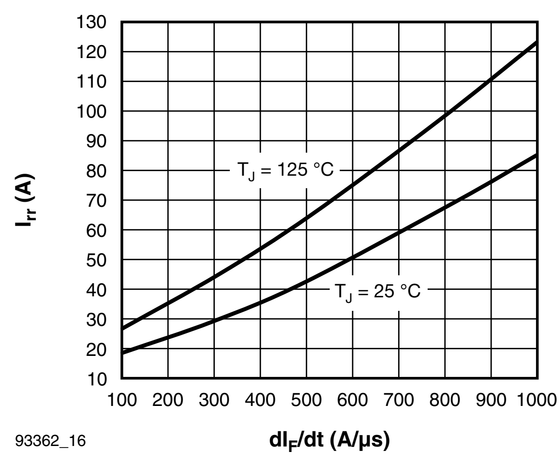


Fig. 16 - Typical Reverse Recovery Current vs. dI_F/dt, V_{CC} = 400 V, I_F = 300 A

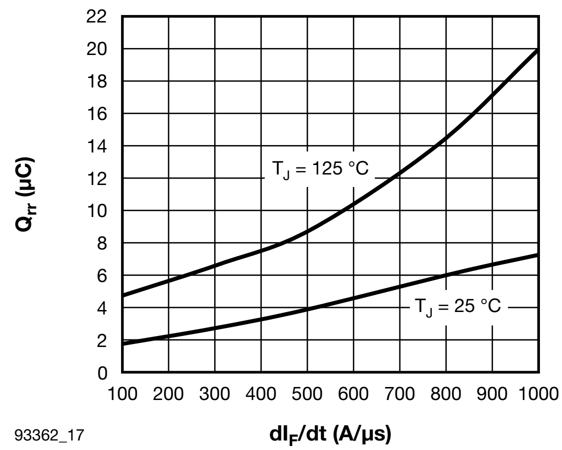


Fig. 17 - Typical Reverse Recovery Charge vs. dI_F/dt, V_{CC} = 400 V, I_F = 300 A

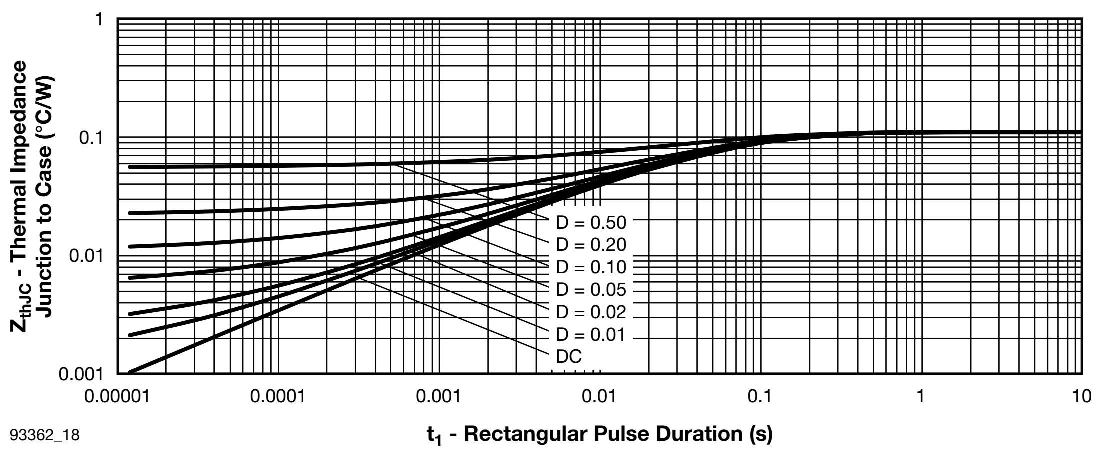


Fig. 18 - Maximum Thermal Impedance Z_{thJC} Characteristics (IGBT)

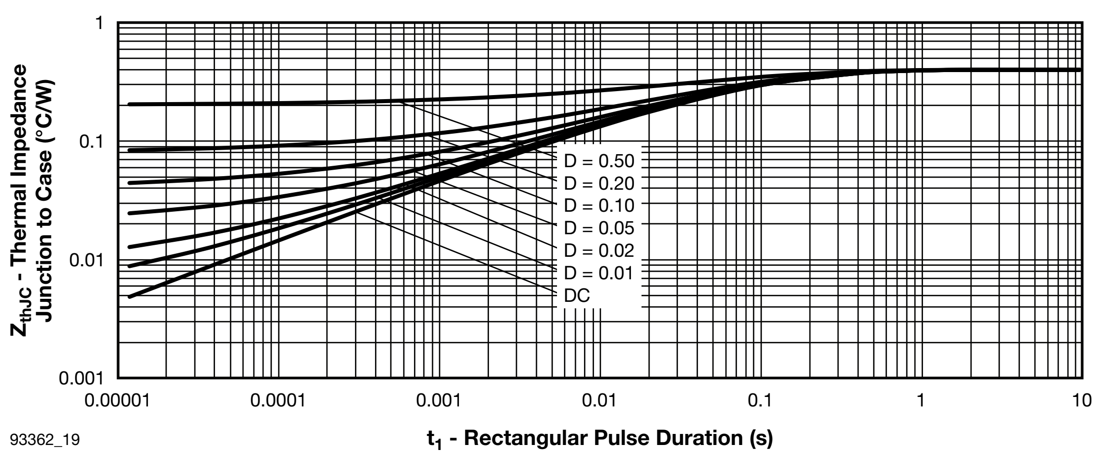


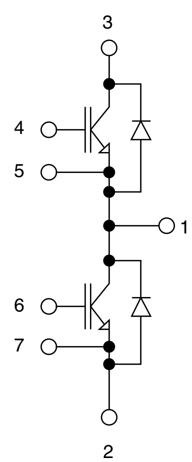
Fig. 19 - Maximum Thermal Impedance Z_{thJC} Characteristics (Diode)

ORDERING INFORMATION TABLE

Device code	G	A	300	T	D	60	S
	1	2	3	4	5	6	7

1 - Insulated Gate Bipolar Transistor (IGBT)
2 - A = Generation 4 IGBT
3 - Current rating (300 = 300 A)
4 - Circuit configuration (T = Half-bridge)
5 - Package indicator (D = Dual INT-A-PAK Low Profile)
6 - Voltage rating (60 = 600 V)
7 - Speed/type (S = Standard Speed IGBT)

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95435

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